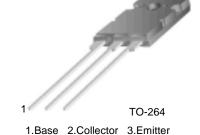


### **FJL6820**

# **High Voltage Color Display Horizontal Deflection Output**

- High Collector-Base Breakdown Voltage : BV<sub>CBO</sub> = 1500V
- Low Saturation Voltage : V<sub>CE</sub>(sat) = 3V (Max.)
- For Color Monitor



## **NPN Triple Diffused Planar Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

| Symbol            | Parameter                 | Rating    | Units |
|-------------------|---------------------------|-----------|-------|
| V <sub>CBO</sub>  | Collector-Base Voltage    | 1500      | V     |
| V <sub>CEO</sub>  | Collector-Emitter Voltage | 750       | V     |
| V <sub>EBO</sub>  | Emitter-Base Voltage      | 6         | V     |
| I <sub>C</sub>    | Collector Current (DC)    | 20        | А     |
| I <sub>CP</sub> * | Collector Current (Pulse) | 30        | А     |
| P <sub>C</sub>    | Collector Dissipation     | 200       | W     |
| T <sub>J</sub>    | Junction Temperature      | 150       | °C    |
| T <sub>STG</sub>  | Storage Temperature       | -55 ~ 150 | °C    |

<sup>\*</sup> Pulse Test: PW=300µs, duty Cycle=2% Pulsed

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

| Symbol                | Parameter                            | Test Conditions                                    | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|--|------|------|------|-------|
| I <sub>CES</sub>      | Collector Cut-off Current            | V <sub>CB</sub> =1400V, R <sub>BE</sub> =0         |      |      | 1    | mA    |
| I <sub>CBO</sub>      | Collector Cut-off Current            | V <sub>CB</sub> =800V, I <sub>E</sub> =0           |      |      | 10   | μΑ    |
| I <sub>EBO</sub>      | Emitter Cut-off Current              | V <sub>EB</sub> =4V, I <sub>C</sub> =0             |      |      | 1    | mA    |
| BV <sub>CBO</sub>     | Collector-Base Breakdown Voltage     | I <sub>C</sub> =500μA, I <sub>E</sub> =0           | 1500 |      |      | V     |
| BV <sub>CEO</sub>     | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> =5mA, I <sub>B</sub> =0             | 750  |      |      | V     |
| BV <sub>EBO</sub>     | Emitter-Base Breakdown Voltage       | I <sub>E</sub> =500μA, I <sub>C</sub> =0           | 6    |      |      | V     |
| h <sub>FE1</sub>      | DC Current Gain                      | V <sub>CE</sub> =5V, I <sub>C</sub> =1A            | 8    |      |      |       |
| h <sub>FE2</sub>      |                                      | $V_{CE}$ =5V, $I_{C}$ =8.5A                        | 6    |      | 10   |       |
| h <sub>FE3</sub>      |                                      | $V_{CE}=5V$ , $I_{C}=11A$                          | 5.5  |      | 8.5  |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | I <sub>C</sub> =11A, I <sub>B</sub> =2.75A         |      |      | 3    | V     |
| V <sub>BE</sub> (sat) | Base-Emitter Saturation Voltage      | I <sub>C</sub> =11A, I <sub>B</sub> =2.75A         |      |      | 1.5  | V     |
| t <sub>STG</sub> *    | Storage Time                         | $V_{CC}$ =200V, $I_{C}$ =10A, $R_{L}$ =20 $\Omega$ |      |      | 3    | μs    |
| t <sub>F</sub> *      | Fall Time                            | I <sub>B1</sub> =2.0A, I <sub>B2</sub> = - 4.0A    |      | 0.15 | 0.2  | μs    |

<sup>\*</sup> Pulse Test: PW=20µs, duty Cycle=1% Pulsed

### Thermal Characteristics T<sub>C</sub>=25°C unless otherwise noted

| Symbol          | Parameter                            | Тур | Max   | Units |
|-----------------|--------------------------------------|-----|-------|-------|
| $R_{\theta jC}$ | Thermal Resistance, Junction to Case |     | 0.625 | °C/W  |

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# **Typical Characteristics**

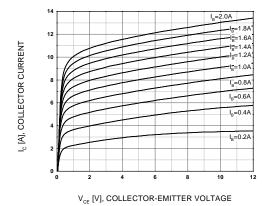


Figure 1. Static Characteristics

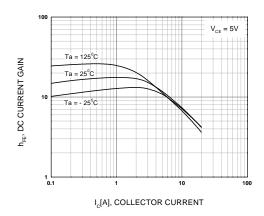


Figure 2. DC Current Gain

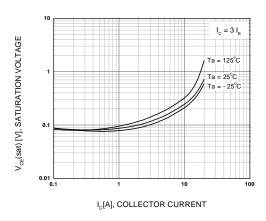


Figure 3. Collector-Emitter Saturation Voltage

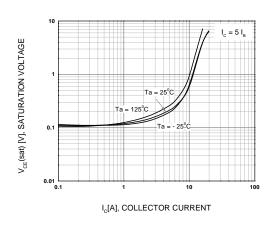


Figure 4. Collector-Emitter Saturation Voltage

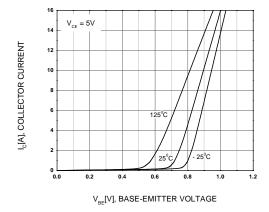


Figure 5. Base-Emitter On Voltage

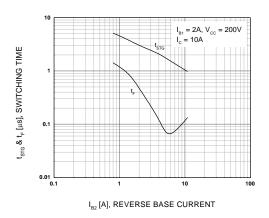


Figure 6. Resistive Load Switching Time

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# Typical Characteristics (Continued)

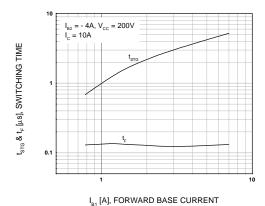
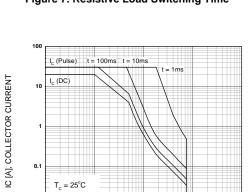


Figure 7. Resistive Load Switching Time



 $V_{CE}^{}$  [V], COLLECTOR-EMITTER VOLTAGE

Figure 9. Forward Bias Safe Operating Area

Single Pulse

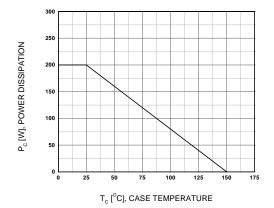


Figure 11. Power Derating

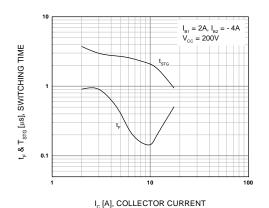
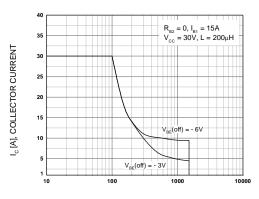


Figure 8. Resistive Load Switching Time

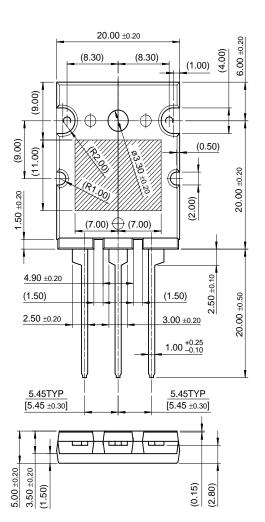


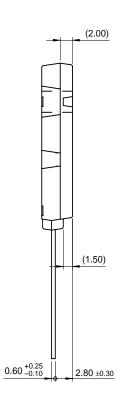
 $V_{\text{CE}}$  [V], COLLECTOR-EMITTER VOLTAGE

Figure 10. Reverse Bias Safe Operating Area

# **Package Demensions**

TO-264





Dimensions in Millimeters

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| CoolFET™             | FRFET™              | $POP^TM$                 | SuperSOT™-8           |
| CROSSVOLT™           | GlobalOptoisolator™ | PowerTrench <sup>®</sup> | SyncFET™              |
| DenseTrench™         | GTO™                | QFET™                    | TinyLogic™            |
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| EcoSPARK™            | ISOPLANAR™          | QT Optoelectronics™      | UltraFET <sup>®</sup> |
| E <sup>2</sup> CMOS™ | LittleFET™          | Quiet Series™            | VCX <sup>TM</sup>     |
| EnSigna™             | MicroFET™           | SLIENT SWITCHER®         |                       |
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